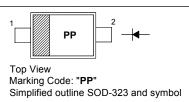
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

For super-high speed switching and wave detection circuit applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25 \, ^{\circ}$ C)

Parameter	Symbol	Value	Unit	
Peak Reverse Voltage	V_{RM}	30	V	
Reverse Voltage	V_{R}	30	V	
Forward Current	I _F	30	mA	
Peak Forward Current	I _{FM}	150	mA	
Junction Temperature	T _j	125	°C	
Storage Temperature Range	T _s	- 55 to + 125	°C	

Characteristics at T_a = 25 °C

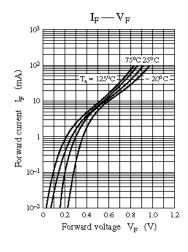
Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at I _F = 1 mA at I _F = 30 mA	V _F	- -	0.4 1	V
Reverse Current at V _R = 30 V	I _R	-	0.3	μΑ
Terminal Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$	Ст	1.5	-	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{rr} = 1$ mA, $R_L = 100$ Ω	t _{rr}	1	-	ns
Detection Efficiency at V_{in} = 3 $V_{(peak)}$, f = 30 MHz, R_L = 3.9 K Ω , C_L = 10 pF	η	65	-	%

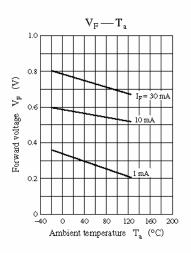


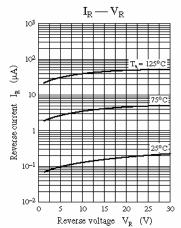


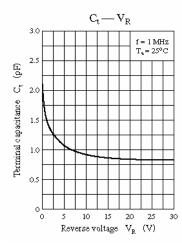


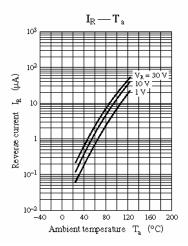














(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 01/09/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

